

ABSTRACT OF THE DISCLOSURE

A polishing pad is cleaned of Cu CMP by-products, subsequent to planarizing a wafer, to reduce pad-glazing by applying to the polishing pad surface a composition comprising about 0.1 to about 3.0 wt.% of at least one organic compound having one or more amine or amide groups, an acid or a base in an amount sufficient to adjust the pH of the composition to about 5.0 to about 12.0, the remainder water. Embodiments comprise ex situ cleaning of a rotating polishing pad by applying a solution having a pH of about 5.0 to about 12.0 at a flow rate of about 100 to about 600 ml/min. for about 3 to about 20 seconds after polishing a wafer having a Cu-containing surface and then removing the cleaning solution from the polishing pad by high pressure rinsing with water.